

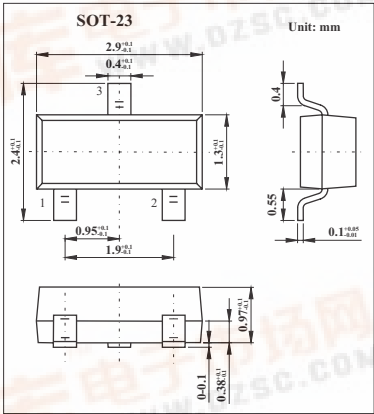
SMD Type

Diodes

Schottky Barrier Diode
KB411D(RB411D)

Features

- Small surface mounting type
- Low VF. (VF=0.43V Typ. at 0.5A)
- High reliability.
- Silicon epitaxial planar



Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Reverse voltage	VRM	40	V
DC Reverse voltage	VR	20	V
Mean rectifying current	Io	0.5	A
Forward current surge peak	IFSM	3	A
Junction temperature	Tj	125	°C
Storage temperature	Tstg	-40 to +125	°C

Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Forward voltage	VF1	IF=500mA			0.50	V
	VF2	IF=10mA			0.30	V
Reverse current	IR1	VR=10V			30	μ A
Capacitance between terminal	CT	VR=10V , f=1MHz		20		pF

Marking

Marking	D3E
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